R M Biefeld

List of Publications by Year
in descending order

49 papers	1,643 citations	318942 23 h-index	312153 41 g-index
50 all docs	50 docs citations	50 times ranked	796 citing authors

#	Article	IF	Citations
1	Growth, Properties and Infrared Device Characteristics of Strained InAsSb-Based Materials. , 2001, , 205-232.		1
2	Exploring new active regions for type I InAsSb strained-layer lasers. Journal of Electronic Materials, 2000, 29, 91-93.	1.0	3
3	The band-gap bowing of AlxGa1â^'xN alloys. Applied Physics Letters, 1999, 74, 3344-3346.	1.5	172
4	The Growth of InAsSb/InAs/InPSb/InAs Mid-Infrared Emitters by Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1999, 607, 303.	0.1	2
5	The growth of AlInSb by metalorganic chemical vapor deposition. Journal of Electronic Materials, 1998, 27, L43-L46.	1.0	9
6	High slope efficiency, â€œcascadedâ€•midinfrared lasers with type I InAsSb quantum wells. Applied Physics Letters, 1998, 72, 2093-2095.	1.5	29
7	Midinfrared lasers and light-emitting diodes with InAsSb/InAsP strained-layer superlattice active regions. Applied Physics Letters, 1997, 70, 3188-3190.	1.5	45
8	Recent Progress in the Growth of Mid-ir Emitters by Metalorganic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1997, 484, 19.	0.1	0
9	The effect of H2 on morphology evolution during GaN metalorganic chemical vapor deposition. Applied Physics Letters, 1997, 71, 3114-3116.	1.5	167
10	The growth of InAsSb/InAsP strained-layer superlattices for use in infrared emitters. Journal of Electronic Materials, 1997, 26, 1225-1230.	1.0	8
11	The metalorganic chemical vapor deposition growth of AlAsSb and InAsSb/InAs using novel source materials for Infrared Emitters. Journal of Electronic Materials, 1997, 26, 903-909.	1.0	15
12	InAsSbâ€based midâ€infrared lasers (3.8â€“3.9 Î¼m) and lightâ€emitting diodes with AlAsSb claddings and semimetal electron injection, grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 69, 465-467.	1.5	74
13	The Growth and Doping of Al(As)Sb by Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1996, 421, 33.	0.1	0
14	Novel Mid-Infrared Lasers with Compressively Strained InAsSb Active Regions. Materials Research Society Symposia Proceedings, 1996, 450, 23.	0.1	0
15	Preparation of AlAsSb and Mid-Infrared (3â€“5Î¼m) Lasers By Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1996, 450, 43.	0.1	0
16	Pseudomorphic InAsSb multiple quantum well injection laser emitting at 3.5 Î¼m. Applied Physics Letters, 1996, 68, 1332-1334.	1.5	52
17	The Growth and Optimization of InPSb/InGaAs/InAsSb Strained-Layer Superlattice Emitters by Metal Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 379, 283.	0.1	2
18	Microstructures of InAs1â^'xSbx (x = 0.07â€“0.14) alloys and strained-layer superlattices. Journal of Electronic Materials, 1995, 24, 819-825.	1.0	28

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19	Modification of valence-band symmetry and Auger threshold energy in biaxially compressedInAs1â^'xSbx. Physical Review B, 1995, 51, 7310-7313.	1.1	17
20	Magnetoâ€optical determination of lightâ€heavy hole splittings in Asâ€rich, InAsSb alloys and superlattices. Applied Physics Letters, 1995, 67, 3331-3333.	1.5	17
21	Magnetophotoluminescence of biaxially compressed InAsSb quantum wells. Applied Physics Letters, 1995, 66, 364-366.	1.5	40
22	Midwave (4 Î¼m) infrared lasers and lightâ€emitting diodes with biaxially compressed InAsSb active regions. Applied Physics Letters, 1994, 64, 812-814.	1.5	84
23	The Optimization of Interfaces in InAsSb/InGaAs Strained-Layer Superlattices grown by Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1994, 340, 247.	0.1	3
24	The Growth of InAsSb/InGaAs Strained-Layer Superlattices by Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1993, 325, 493.	0.1	3
25	Ordering-induced band-gap reduction inInAs1â^'xSbx(xâ‰Š0.4) alloys and superlattices. Physical Review B, 1992, 46, 1909-1912.	1.1	80
26	Infrared magneto-optical and photoluminescence studies of the electronic properties of In(As,Sb) strained-layer superlattices. Physical Review B, 1991, 44, 1143-1149.	1.1	32
27	The Preparation of InAsSb/InSb SLS and InSb Photodiodes by MOCVD. Materials Research Society Symposia Proceedings, 1990, 216, 175.	0.1	10
28	MOCVD-grown InAsSb strained-layer superlattice infrared detectors with photoresponses â©¾10Î¼m. Semiconductor Science and Technology, 1990, 5, S24-S26.	1.0	13
29	Doping andp-n junction formation in InAs1-xSbx/InSb SLSâ€™s by MOCVD. Journal of Electronic Materials, 1989, 18, 775-780.	1.0	27
30	High photoconductive gain in lateral InAsSb strainedâ€layer superlattice infrared detectors. Applied Physics Letters, 1988, 53, 1961-1963.	1.5	38
31	Extended infrared response of InAsSb strainedâ€layer superlattices. Applied Physics Letters, 1988, 52, 831-833.	1.5	52
32	Planar channeling in superlattices. II. Catastrophic dechanneling. Physical Review B, 1988, 38, 11086-11097.	1.1	21
33	Photoluminescence and the band structure of InAsSb strainedâ€layer superlattices. Applied Physics Letters, 1988, 53, 216-218.	1.5	54
34	The preparation of modulation-doped GaAs/GaAs1-xPx strained-layer superlattices by metal organic chemical vapor deposition. Journal of Electronic Materials, 1987, 16, 335-340.	1.0	2
35	The use of metalorganic chemical vapor deposition to prepare device quality Ga(AsP) strained-layer superlattices. Journal of Electronic Materials, 1986, 15, 193-199.	1.0	14
36	Characterization of ionâ€implantation doping of strainedâ€layer superlattices. I. Structural properties. Journal of Applied Physics, 1986, 60, 3631-3640.	1.1	19

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37	Incident-Angle Dependence of Catastrophic Dechanneling for Strained-Layer Superlattices. Physical Review Letters, 1985, 54, 2355-2358.	2.9	43
38	The Effect of Hydrostatic Pressure on Trapping Centers in Strained-Layer Superlattice Structures. , 1985, , 527-530.		1
39	Photoluminescent and electroluminescent properties of GaAs1â^'xPxâ€GaAs1â^'yPyisotype heterojunction electrodes. Applied Physics Letters, 1984, 45, 150-152.	1.5	9
40	Depth profiles of perpendicular and parallel strain in a GaAsxP1â^'x/GaP superlattice. Applied Physics Letters, 1984, 45, 223-225.	1.5	25
41	Resonance between the Wavelength of Planar-Channeled Particles and the Period of Strained-Layer Superlattices. Physical Review Letters, 1984, 52, 125-128.	2.9	52
42	Comparison of trapping levels in GaAsP strainedâ€layer superlattice structures and in their buffer layers. Applied Physics Letters, 1984, 45, 408-410.	1.5	7
43	Strain measurements by channeling angular scans. Applied Physics Letters, 1983, 43, 1020-1022.	1.5	61
44	Independently variable band gaps and lattice constants in GaAsP strainedâ€layer superlattices. Applied Physics Letters, 1983, 43, 759-761.	1.5	25
45	Resonance between Channeled Particle Wavelengths and Periodicity of Strained-Layer Superlattices. Materials Research Society Symposia Proceedings, 1983, 25, 483.	0.1	0
46	A GaAsxP1â^'x/GaP strainedâ€layer superlattice. Applied Physics Letters, 1982, 41, 172-174.	1.5	158
47	Ionic Conductivity of Li2â€‰Oâ€‰â€‰â€‰Based Mixed Oxides and the Effects of Moisture and LiOH on Their Electrical and Structural Properties. Journal of the Electrochemical Society, 1979, 126, 1-6.	1.3	50
48	Percolative ionic conduction in the LiAlSiO4glass-ceramic system. Physical Review B, 1977, 15, 5912-5920.	1.1	22
49	Ionic Conductivity in Solid Electrolytes Based on Lithium Aluminosilicate Glass and Glassâ€Ceramic. Journal of the Electrochemical Society, 1976, 123, 680-687.	1.3	57